

# NTZD3158P

## Small Signal MOSFET

-20 V, -430 mA, Dual P-Channel with ESD Protection, SOT-563

### Features

- Low  $R_{DS(on)}$  Improving System Efficiency
- Low Threshold Voltage
- ESD Protected Gate
- Small Footprint 1.6 x 1.6 mm
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted.)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	-20	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 6.0$	V	
Continuous Drain Current (Note 1)	Steady State	$I_D$	$T_A = 25^\circ\text{C}$	-430	mA
			$T_A = 85^\circ\text{C}$	-310	
Power Dissipation (Note 1)	Steady State	$P_D$	250	mW	
Continuous Drain Current (Note 1)	$t \leq 5\text{ s}$	$I_D$	$T_A = 25^\circ\text{C}$	-455	mA
			$T_A = 85^\circ\text{C}$	-328	
Power Dissipation (Note 1)	$t \leq 5\text{ s}$	$P_D$	280	mW	
Pulsed Drain Current	$t_p = 10\ \mu\text{s}$	$I_{DM}$	-750	mA	
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	-350	mA	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - $t \leq 5\text{ s}$ (Note 1)		447	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

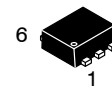
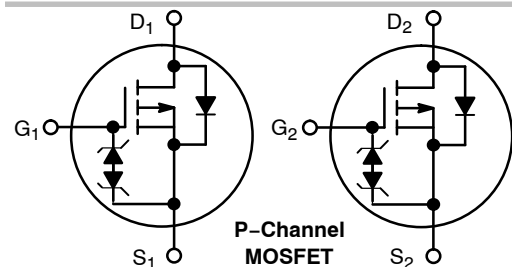
1. Surface mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in. sq. [1 oz.] including traces).



ON Semiconductor®

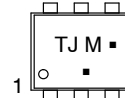
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	$I_D$ Max
-20 V	0.5 $\Omega$ @ -4.5 V	-430 mA
	0.6 $\Omega$ @ -2.5 V	
	1.0 $\Omega$ @ -1.8 V	



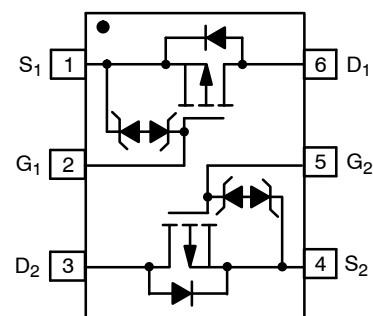
SOT-563-6  
CASE 463A

### MARKING DIAGRAM



$T_J$  = Specific Device Code  
 $M$  = Date Code  
 ■ = Pb-Free Package  
 (Note: Microdot may be in either location)

### PINOUT: SOT-563



Top View

### ORDERING INFORMATION

Device	Package	Shipping†
NTZD3158PT1G	SOT-563 (Pb-Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTZD3158P

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted.)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			18		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, T <sub>J</sub> = 25°C			-1.0	μA
		V <sub>DS</sub> = -16 V, T <sub>J</sub> = 125°C			-2.0	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V			±2.0	μA

## ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250 μA	-0.45		-1.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			-1.9		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -430 mA		0.5	0.9	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -300 mA		0.6	1.2	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -150 mA		1.0	2.0	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -430 mA		1.0		S

## CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -16 V		105	175	pF
Output Capacitance	C <sub>OSS</sub>			15	30	
Reverse Transfer Capacitance	C <sub>RSS</sub>			10	20	
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -215 mA		1.7	2.5	nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			0.1		
Gate-to-Source Charge	Q <sub>GS</sub>			0.3		
Gate-to-Drain Charge	Q <sub>GD</sub>			0.4		

## SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -10 V, I <sub>D</sub> = -215 mA, R <sub>G</sub> = 10 Ω		10		ns
Rise Time	t <sub>r</sub>			12		
Turn-Off Delay Time	t <sub>d(off)</sub>			35		
Fall Time	t <sub>f</sub>			19		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -350 mA	T <sub>J</sub> = 25°C		-0.8	-1.2	V
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>SD</sub> /dt = 100 A/μs, I <sub>S</sub> = -350 mA			13		ns

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

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## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

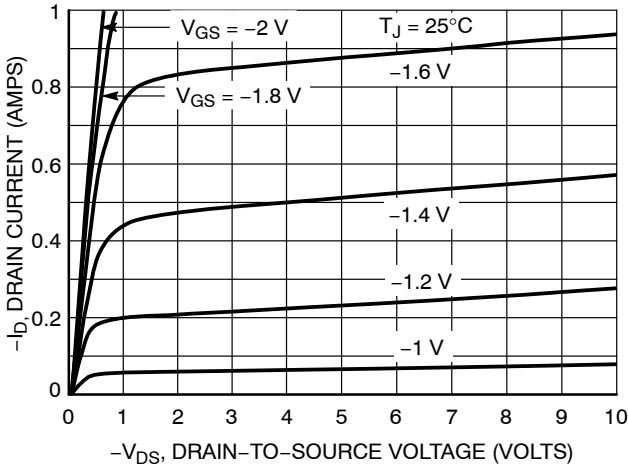


Figure 1. On-Region Characteristics

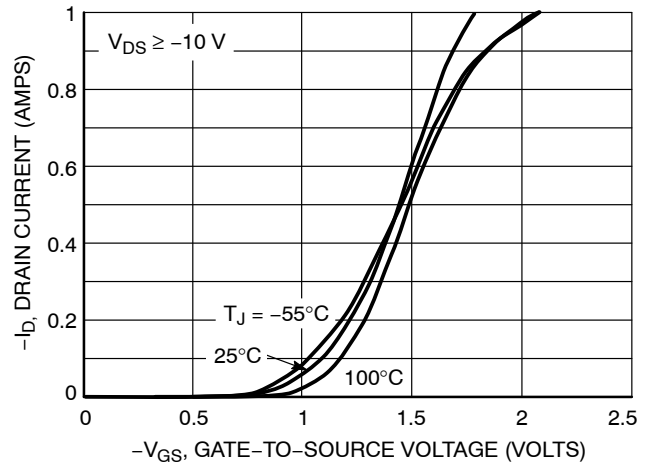


Figure 2. Transfer Characteristics

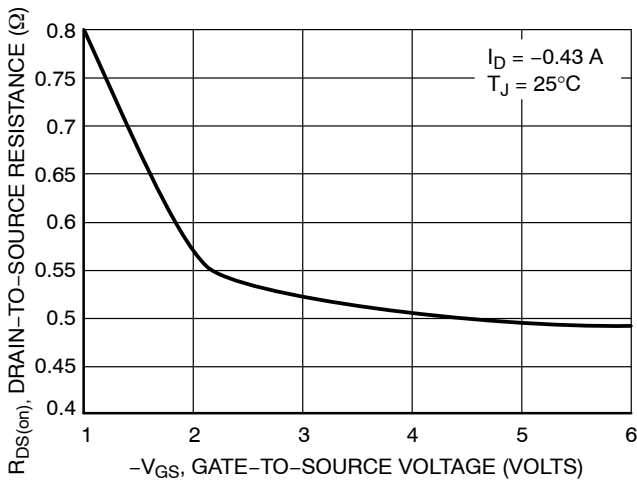


Figure 3. On-Resistance vs. Gate-to-Source Voltage

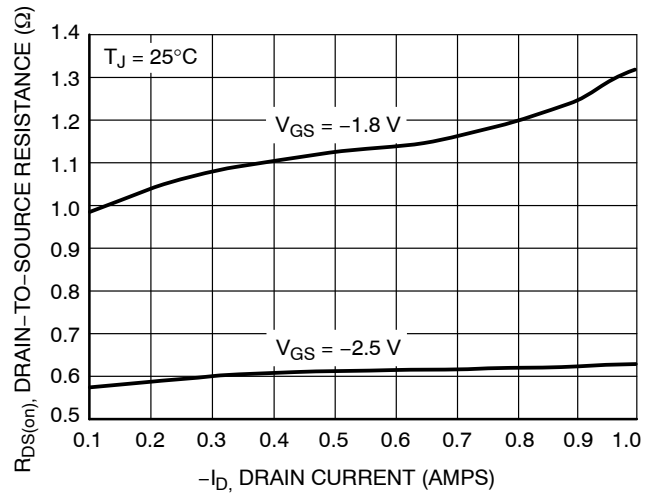


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

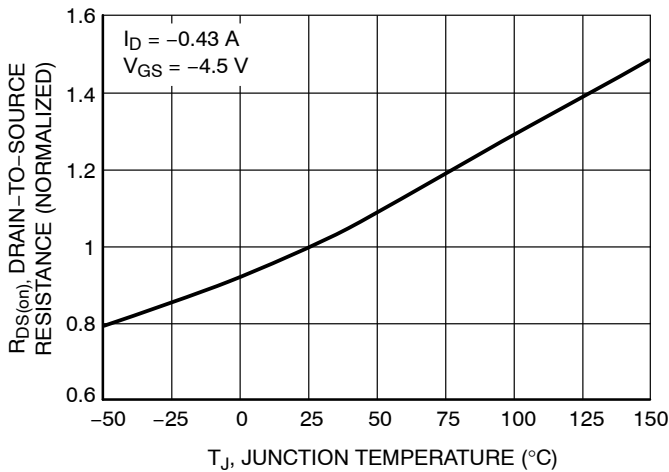


Figure 5. On-Resistance Variation with Temperature

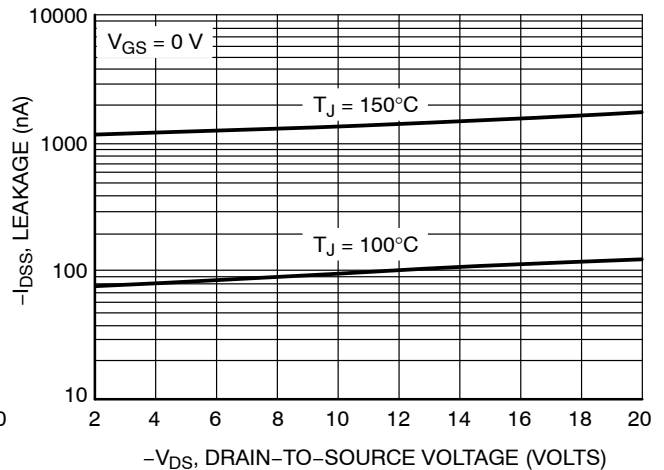


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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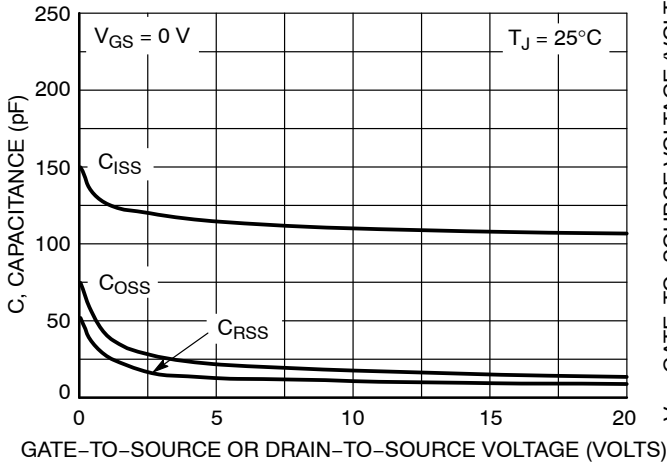


Figure 7. Capacitance Variation

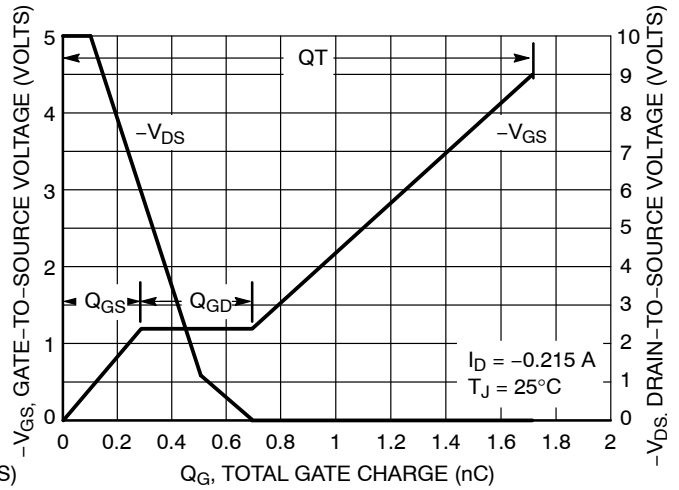


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

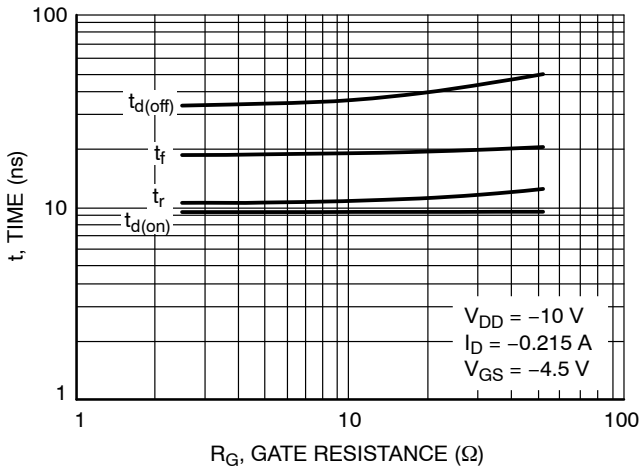


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

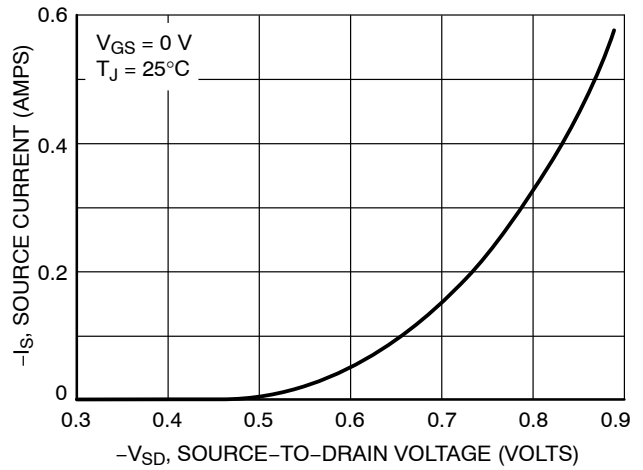
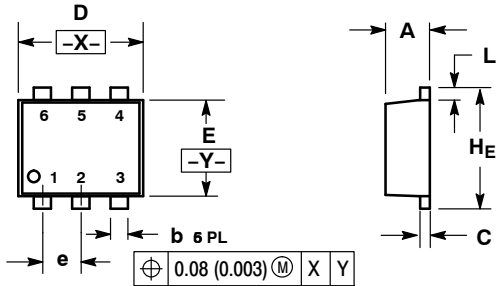


Figure 10. Diode Forward Voltage vs. Current

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## PACKAGE DIMENSIONS

### SOT-563, 6 LEAD CASE 463A ISSUE F

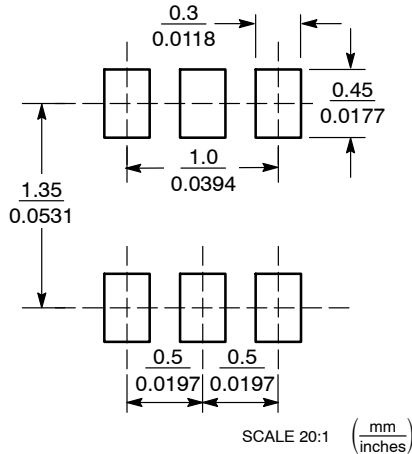


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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